

## R-C Thermal Model Parameters

### DESCRIPTION

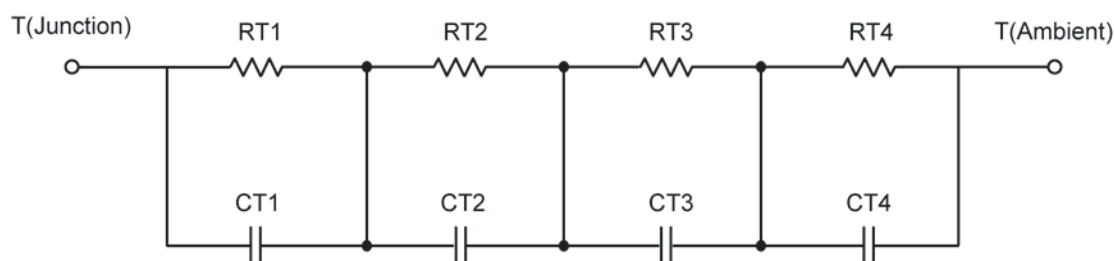
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	10.2656	N/A	7.2424
RT2	32.3224	N/A	4.1194
RT3	32.5441	N/A	19.2549
RT4	34.8679	N/A	11.3833
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.2122 m	N/A	5.6371 m
CT2	113.7516 m	N/A	1.3087 m
CT3	6.9378 m	N/A	18.4074 m
CT4	2.5174	N/A	6.3824 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	15.2545	N/A	7.3028
RF2	30.5275	N/A	12.7227
RF3	31.0477	N/A	8.4053
RF4	33.1703	N/A	13.5692
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.1505 m	N/A	791.9614 u
CF2	5.9493 m	N/A	1.7140 m
CF3	95.8584 m	N/A	2.1604 m
CF4	2.4573	N/A	17.6127 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

